

| Ref # | Hits   | Search Query                                      | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|--------|---|---|------------------|---------|------------------|
| L1    | 73244  | HBT heterojunction (bipolar near transistor)      | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/28 15:05 |
| L2    | 219944 | (field near effect near transistor)<br>FET mosfet | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/28 15:06 |
| L3    | 28094  | 1 and 2   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/28 15:07 |
| L16   | 477    | 3 and (InGaP GaInP)                               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/28 17:26 |